## SUBJECT NO-EC29004, SUBJECT NAME- Devices Laboratory

## LTP- 0-0-3,CRD- 2

## SYLLABUS :-

- 1. JFET Characterization
- 2. Diode Breakdown Characteristics
- 3. Capacitance âVoltage Characteristics of a PN Junction (Doping profile)
- 4. High frequency Characteristics of BJT.
- 5. SCR Characteristics.
- 6. Hall Effect.